Sergey V Balakirev

List of Publications by Year
in descending order

20	200	1040056 9	1058476 14
papers	citations	h-index	g-index

20	20	20	41
all docs	docs citations	times ranked	citing authors

#	Article	IF	Citations
1	Low-density arrays of ultra-small InAs nanostructures obtained by two-stage arsenic exposure during droplet epitaxy. Applied Surface Science, 2022, 578, 152023.	6.1	4
2	Independent Control Over Size and Surface Density of Droplet Epitaxial Nanostructures Using Ultra-Low Arsenic Fluxes. Nanomaterials, 2021, 11, 1184.	4.1	8
3	Anomalous behavior of In adatoms during droplet epitaxy on the AlGaAs surfaces. Nanotechnology, 2020, 31, 485604.	2.6	9
4	Mechanism of nucleation and critical layer formation during In/GaAs droplet epitaxy. Nanotechnology, 2019, 30, 505601.	2.6	21
5	Hybrid Analyticalâ€“Monte Carlo Model of In/GaAs(001) Droplet Epitaxy: Theory and Experiment. Physica Status Solidi (B): Basic Research, 2018, 255, 1700360.	1.5	25
6	Droplet epitaxy of In/AlGaAs nanostructures on the As-stabilized surface. Journal of Physics: Conference Series, 2018, 1124, 022018.	0.4	2
7	MBE formation of self-catalyzed GaAs nanowires using ZnO nanosized films. Journal of Physics: Conference Series, 2018, 1124, 081024.	0.4	4
8	Analyticalâ€“Monte Carlo model of the growth of In nanostructures during droplet epitaxy on the triangle-patterned GaAs substrates. Journal of Physics: Conference Series, 2018, 1124, 022001.	0.4	2
9	Formation of nanoscale structures on the surface of gallium arsenide by local anodic oxidation and plasma chemical etching. Journal of Physics: Conference Series, 2018, 1124, 041024.	0.4	1
10	Study of the geometrical parameters of In nanostructures during droplet epitaxy on the As-stabilized GaAs(001) surface. Journal of Physics: Conference Series, 2018, 1124, 022025.	0.4	0
11	Study of Nanoscale Profiling Modes of GaAs Epitaxial Structures by Focused Ion Beams. Nanotechnologies in Russia, 2018, 13, 26-33.	0.7	21
12	Monte Carlo investigation of the MBE growth of GaAs on the surfaces with different crystallographic orientations. Journal of Physics: Conference Series, 2017, 917, 032034.	0.4	1
13	Monte Carlo simulation of the kinetic effects on GaAs/GaAs(001) MBE growth. Journal of Crystal Growth, 2017, 457, 46-51.	1.5	20
14	Droplet epitaxy of GaAs nanostructures on the As-stabilized GaAs(001) surface. Journal of Physics: Conference Series, 2017, 917, 032037.	0.4	12
15	Kinetic Monte Carlo simulation of the indium droplet epitaxy on the Ga-terminated GaAs(001) surface. Journal of Physics: Conference Series, 2017, 917, 032033.	0.4	1
16	Monte Carlo simulation of V/III flux ratio influence on GaAs island nucleation during MBE. Journal of Physics: Conference Series, 2016, 681, 012036.	0.4	15
17	Effect of GaAs native oxide upon the surface morphology during GaAs MBE growth. Journal of Physics: Conference Series, 2016, 741, 012012.	0.4	5
18	Kinetic Monte Carlo simulation of GaAs(001) MBE growth considering the V/III flux ratio effect. Journal of Vacuum Science and Technology B:Nanotechnology and Microelectronics, 2016, 34, 041804.	1.2	15

#	Article	IF	Citations
19	Monte Carlo investigation of the influence of V/III flux ratio on GaAs/GaAs(001) submonolayer epitaxy. Technical Physics, 2016, 61, 971-977.	0.7	16
20	Effect of interaction in the Gaâ€“Asâ€“O system on the morphology of a GaAs surface during molecular-beam epitaxy. Physics of the Solid State, 2016, 58, 1045-1052.	0.6	18